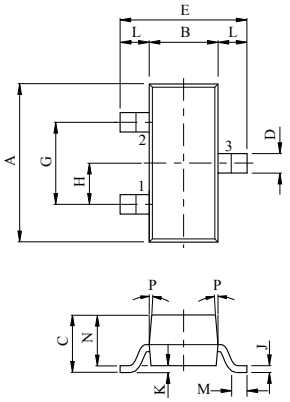
BCW68

EPITAXIAL PLANAR PNP TRANSISTOR

HIGH CURRENT APPLICATION.



DIM	MILLIMETERS
A	2.93±0.20
B	1.30+0.20/-0.15
C	1.30 MAX
D	0.45+0.15/-0.05
E	2.40+0.30/-0.20
G	1.90
H	0.95
J	0.13+0.10/-0.05
K	0.00 ~ 0.10
L	0.55
M	0.20 MIN
N	1.00+0.20/-0.10
P	7 °

1. EMITTER
2. BASE
3. COLLECTOR

SOT-23

MAXIMUM RATING (Ta=25℃)

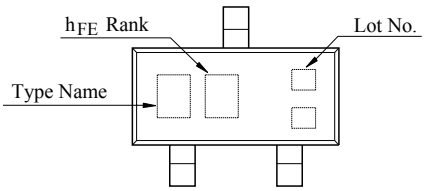
CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-60	V
Collector-Emitter Voltage	V_{CEO}	-45	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-800	mA
Emitter Current	I_E	800	mA
Collector Power Dissipation	P_C *	350	mW
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55 ~ 150	℃

* : Package Mounted On 99.9% Alumina 10 × 8 × 0.6mm.

MARK SPEC

TYPE	MARK
BCW68F	DF
BCW68G	DG

Marking



ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Emitter Breakdown Voltage		$V_{(BR)CEO}$	I_C=-10mA, I_B=0	-45	-	-	V
Emitter-Base Breakdown Voltage		$V_{(BR)EBO}$	I_E=10μA, I_C=0	-5.0	-	-	V
Collector Cut-off Current		I_{CES}	V_{EB}=0V, V_{CE}=-45V	-	-	-20	nA
			Ta=150℃, V_{EB}=0V, V_{CE}=-45V	-	-	-20	μA
Emitter Cut-off Current		I_{EBO}	I_C=0, V_{EB}=-4V	-	-	-20	nA
DC Current Gain	Group F	h_{FE}	V_{CE}=-1V, I_C=-10mA	75	-	-	
	Group G			120	-	-	
	Group F		V_{CE}=-1V, I_C=-100mA	100	-	250	
	Group G			160	-	400	
	Group F		V_{CE}=-1V, I_C=-500mA	35	-	-	
	Group G			60		-	
Base-Emitter Saturation Voltage		$V_{BE(sat)}$	I_C=-100mA, I_B=-10mA	-	-	-1.25	V
			I_C=-500mA, I_B=-50mA	-	-	-2.0	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	I_C=-100mA, I_B=-10mA	-	-	-0.3	V
			I_C=-500mA, I_B=-50mA	-	-	-0.7	
Transition Frequency		f_T	I_C=-80mA, V_{CE}=-10V, f=100MHz	100	-	-	MHz
Collector Output Capacitance		C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz	-	-	18	pF
Collector Input Capacitance		C_{ib}	V_{EB}=-0.5V, f=1MHz	-	-	80	pF
Noise Figure		NF	I_C=-0.2mA, V_{CE}=-5V, Rg=1kΩ, f=1kHz	-	2.0	10	dB